

EPIGAP Optronik GmbH

Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de



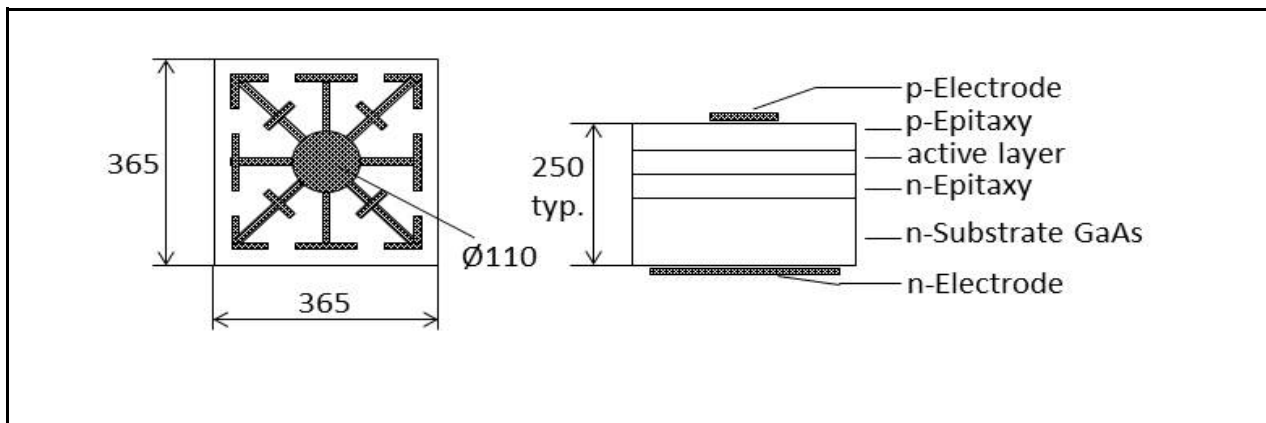
Data Sheet

LED Chip Infrared

EOLC-1060-17-1

Rev. 04, 2017

Radiation	Type	Electrodes
Infrared	MQW / GaAs	P (anode) up



Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.15	1.3	V
Forward voltage	$I_F = 100 \text{ mA}$	V_F		1.25	1.4	V
Reverse current	$I_R = 5 \text{ V}$	I_R			10	μA
Output power*	$I_F = 50 \text{ mA}$	Φ_e	3.5	4		mW
Radiant intensity	$I_F = 100 \text{ mA}$	I_e		1		mW/sr
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	1040	1060	1080	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		80		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 031



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.